

**MMBC1623L6****NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

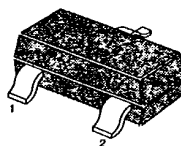
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	50	V
Collector-Emitter Voltage	$V_{CE0}$	40	V
Emitter-Base Voltage	$V_{EB0}$	5.0	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBC1623L3 for graphs

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CB0}$	$V_{CB} = 40\text{V}, I_E = 0$		100	nA
Emitter Cutoff Current	$I_{EB0}$	$V_{EB} = 5\text{V}, I_C = 0$		100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = 6\text{V}, I_C = 1.0\text{mA}$	200	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}, I_B = 10\text{mA}$		0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 100\text{mA}, I_B = 10\text{mA}$		1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = 1.0\text{mA}, V_{CE} = 6\text{V}$	0.6	0.7	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 6\text{V}, I_E = 10\text{mA}$ $f = 100\text{MHz}$	200		MHz

SOT-23



1. Base 2. Emitter 3. Collector

**Marking**